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(54) Title (EN): PHASE TRANSITION THIN FILM DEVICE

(54) Title (FR): DISPOSITIF À FILM MINCE À TRANSITION DE PHASE

(57) Abstract:

(EN): The disclosed device comprises a thin film layer (4) of a phase transition material disposed over a substrate (2), and a confinement layer (3) adjacent to the thin film layer. The thin film layer has first and second in-plane lattice parameters and an out-of-plane lattice parameter when undergoing the phase transition, and the confinement layer has first and second in-plane layer lattice parameters and an out-of-plane layer lattice parameter. The confinement layer lattice parameters are within a range which allows to control the onset of and/or block the phase transition.

(FR): Le dispositif selon la présente invention comprend une couche de film mince (4) d'un matériau de transition de phase disposé sur un substrat (2), et une couche de confinement (3) adjacente à la couche de film mince. La couche de film mince comprend des premier et second paramètres de réseau dans le plan et un paramètre de réseau hors plan lors de sa soumission à la transition de phase, et la couche de confinement comprend des premier et second paramètres de réseau de couche dans le plan et un paramètre de réseau de couche hors plan. Les paramètres de réseau de la couche de confinement s'inscrivent dans une plage permettant de commander le déclenchement et/ou le blocage de la transition de phase.

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